



ON Semiconductor®

FDP18N50 / FDPF18N50 / FDPF18N50T

N-Channel UniFET™ MOSFET

500 V, 18 A, 265 mΩ

Features

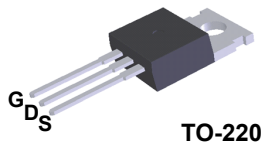
- $R_{DS(on)} = 220 \text{ m}\Omega$ (Typ.) @ $V_{GS} = 10 \text{ V}$, $I_D = 9 \text{ A}$
- Low Gate Charge (Typ. 45 nC)
- Low C_{rss} (Typ. 25 pF)
- 100% Avalanche Tested

Applications

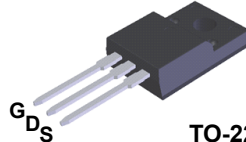
- LCD/LED/PDP TV
- Lighting
- Uninterruptible Power Supply

Description

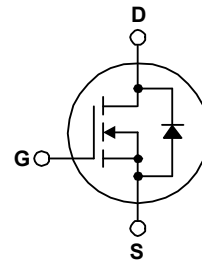
UniFET™ MOSFET is ON Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.



TO-220



TO-220F



Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter		FDP18N50	FDPF18N50 / FDPF18N50T	Unit
V_{DSS}	Drain-Source Voltage		500		V
I_D	Drain Current	- Continuous ($T_C = 25^\circ\text{C}$)	18	18 *	A
		- Continuous ($T_C = 100^\circ\text{C}$)	10.8	10.8 *	A
I_{DM}	Drain Current	- Pulsed (Note 1)	72	72 *	A
V_{GSS}	Gate-Source voltage		± 30		V
E_{AS}	Single Pulsed Avalanche Energy	(Note 2)	945		mJ
I_{AR}	Avalanche Current	(Note 1)	18		A
E_{AR}	Repetitive Avalanche Energy	(Note 1)	23.5		mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	4.5		V/ns
P_D	Power Dissipation	($T_C = 25^\circ\text{C}$)	235	38.5	W
		- Derate Above 25°C	1.88	0.3	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150		$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds		300		$^\circ\text{C}$

* Drain current limited by maximum junction temperature

Thermal Characteristics

Symbol	Parameter		FDP18N50	FDPF18N50 / FDPF18N50T	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.		0.53	3.3	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.		62.5	62.5	$^\circ\text{C/W}$

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDP18N50	FDP18N50	TO-220	Tube	N/A	N/A	50 units
FDPF18N50	FDPF18N50	TO-220F	Tube	N/A	N/A	50 units
FDPF18N50T	FDPF18N50T	TO-220F	Tube	N/A	N/A	50 units

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Typ.	Max	Unit
Off Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0 V, I _D = 250 μA	500	--	--	V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C	--	0.5	--	V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 500 V, V _{GS} = 0 V V _{DS} = 400 V, T _C = 125°C	-- --	-- --	1 10	μA μA
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30 V, V _{DS} = 0 V	--	--	100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -30 V, V _{DS} = 0 V	--	--	-100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250 μA	3.0	--	5.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 9 A	--	0.220	0.265	Ω
g _{FS}	Forward Transconductance	V _{DS} = 40 V, I _D = 9 A	--	25	--	S
Dynamic Characteristics						
C _{iSS}	Input Capacitance	V _{DS} = 25 V, V _{GS} = 0 V, f = 1 MHz	--	2200	2860	pF
C _{oSS}	Output Capacitance		--	330	430	pF
C _{rSS}	Reverse Transfer Capacitance		--	25	40	pF
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{DD} = 250 V, I _D = 18 A, V _{GS} = 10 V, R _G = 25 Ω	--	55	120	ns
t _r	Turn-On Rise Time		--	165	340	ns
t _{d(off)}	Turn-Off Delay Time		--	95	200	ns
t _f	Turn-Off Fall Time		--	90	190	ns
Q _g	Total Gate Charge	V _{DS} = 400 V, I _D = 18 A, V _{GS} = 10 V	--	45	60	nC
Q _{gs}	Gate-Source Charge		--	12.5	--	nC
Q _{gd}	Gate-Drain Charge		--	19	--	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain-Source Diode Forward Current		--	--	18	A
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	72	A
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 18 A	--	--	1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 18 A, dI _F /dt =100 A/μs	--	500	--	ns
Q _{rr}	Reverse Recovery Charge		--	5.4	--	μC

Notes:

1. Repetitive rating: pulse-width limited by maximum junction temperature.
2. $L = 5.2\text{ mH}$, $I_{AS} = 18\text{ A}$, $V_{DD} = 50\text{ V}$, $R_G = 25\text{ }\Omega$, starting $T_J = 25^\circ\text{C}$.
3. $I_{SD} \leq 18\text{ A}$, $di/dt \leq 200\text{ A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, starting $T_J = 25^\circ\text{C}$.
4. Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

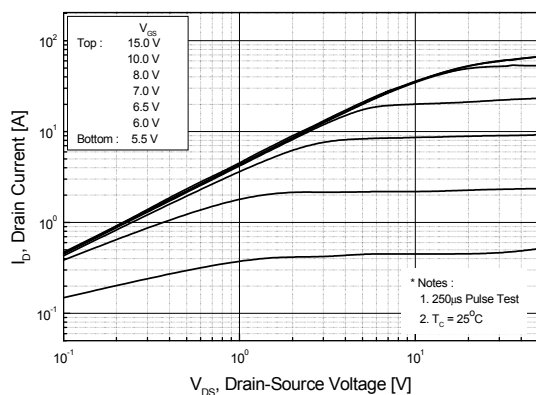


Figure 2. Transfer Characteristics

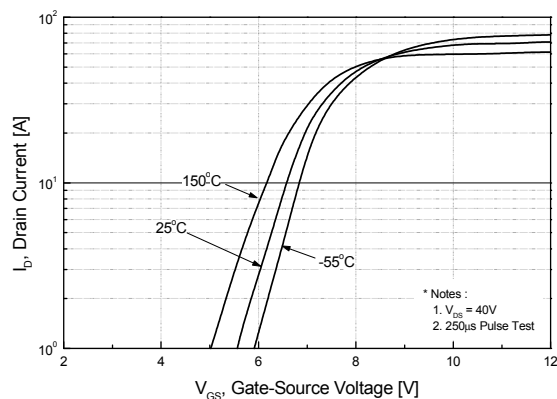


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

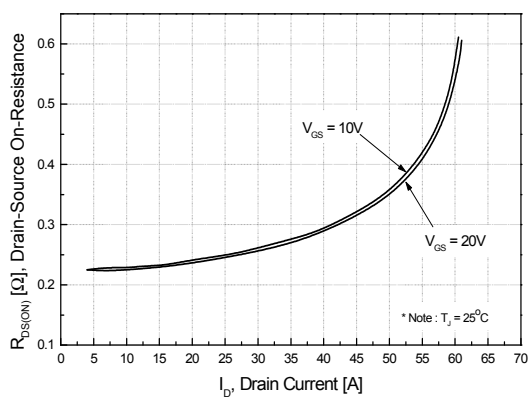


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

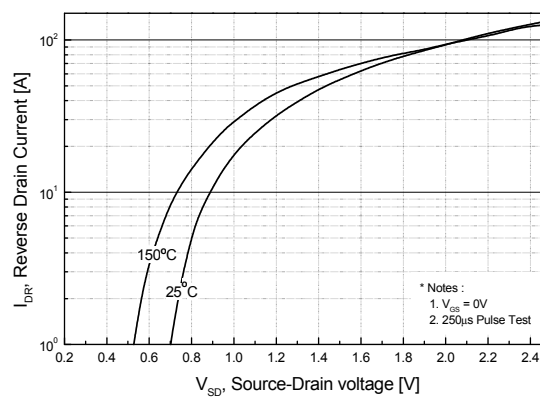


Figure 5. Capacitance Characteristics

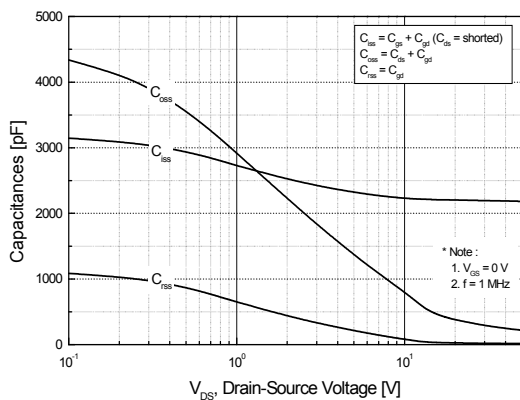
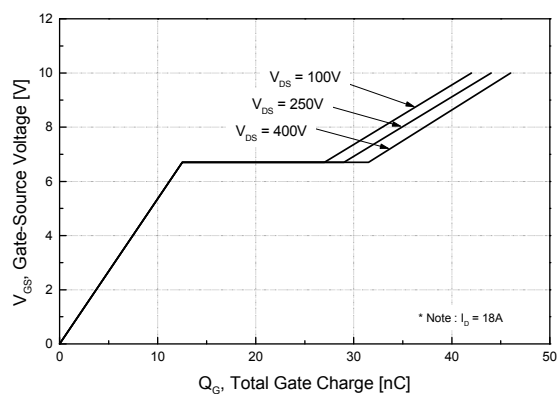


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

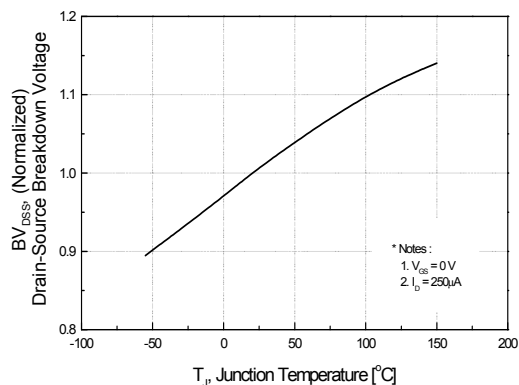


Figure 8. On-Resistance Variation vs. Temperature

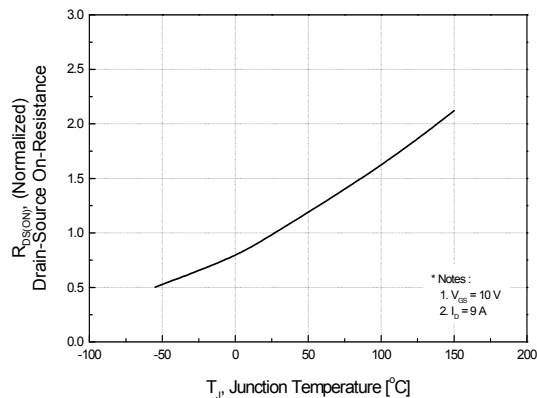


Figure 9-1. Maximum Safe Operating Area - FDP18N50

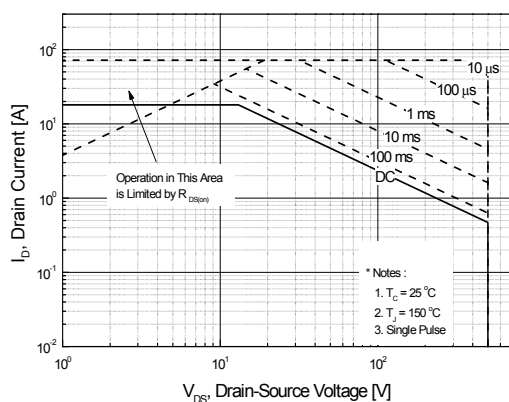


Figure 9-2. Maximum Safe Operating Area - FDPF18N50 / FDPF18N50T

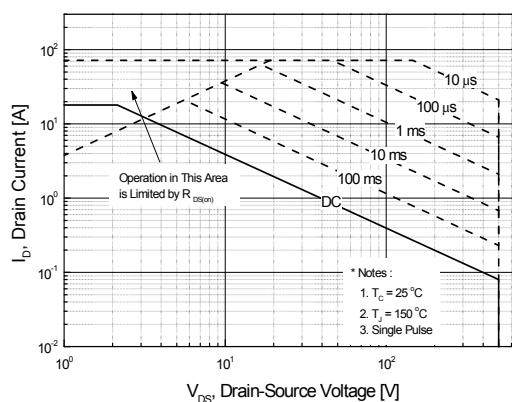
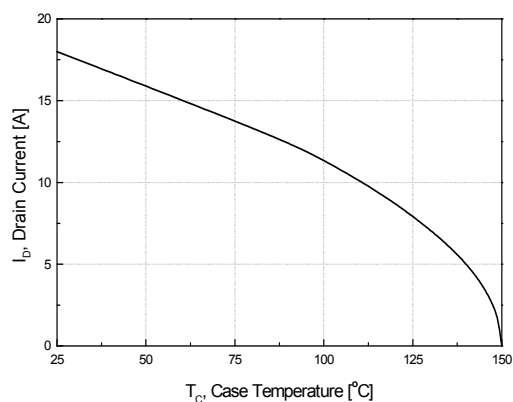


Figure 10. Maximum Drain Current vs. Case Temperature



Typical Performance Characteristics (Continued)

Figure 11-1. Transient Thermal Response Curve - FDP18N50

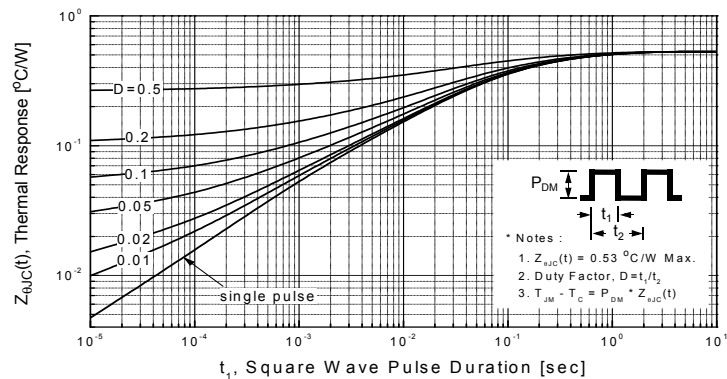
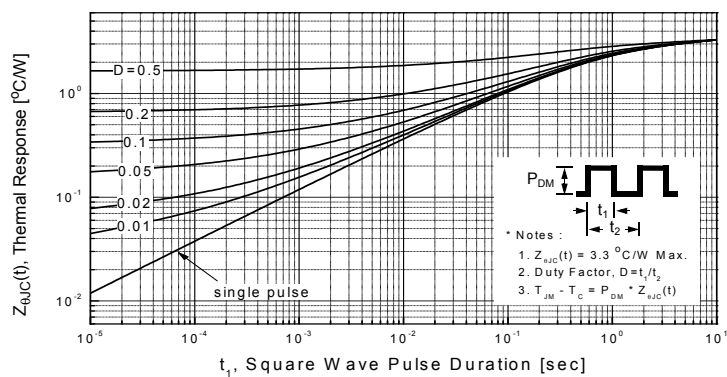


Figure 11-2. Transient Thermal Response Curve - FDPF18N50 / FDPF18N50T



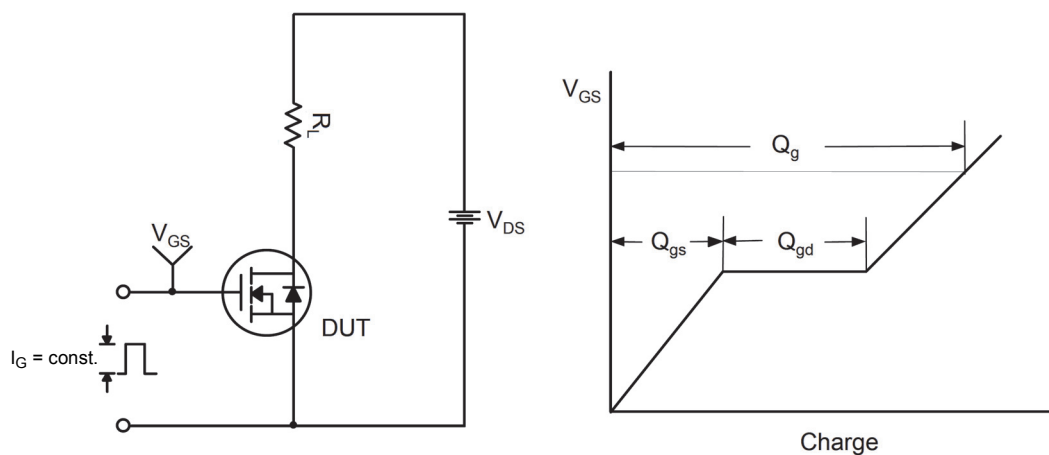


Figure 12. Gate Charge Test Circuit & Waveform

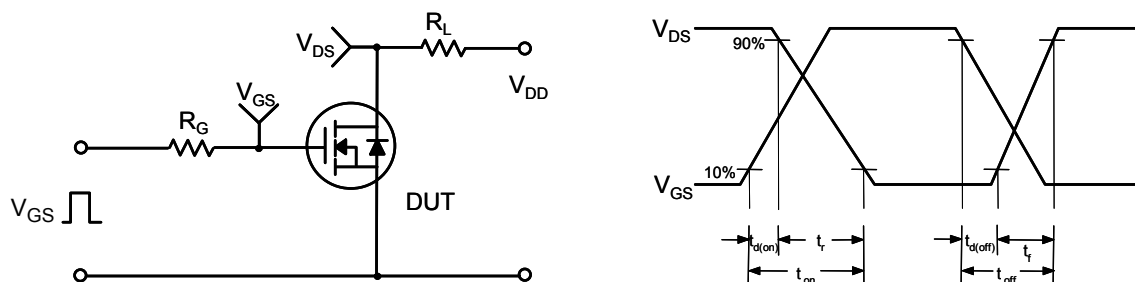


Figure 13. Resistive Switching Test Circuit & Waveforms



Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

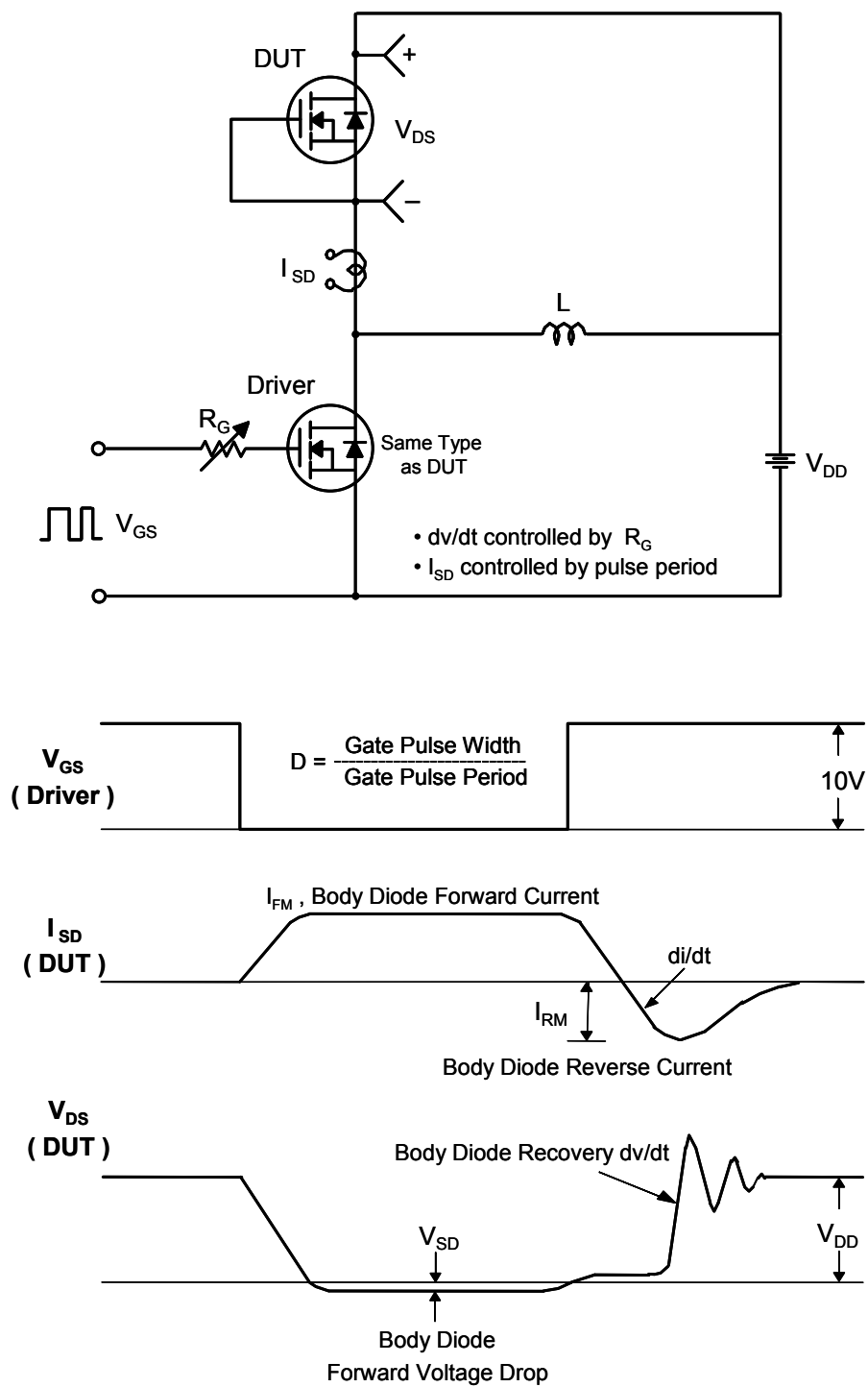


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions

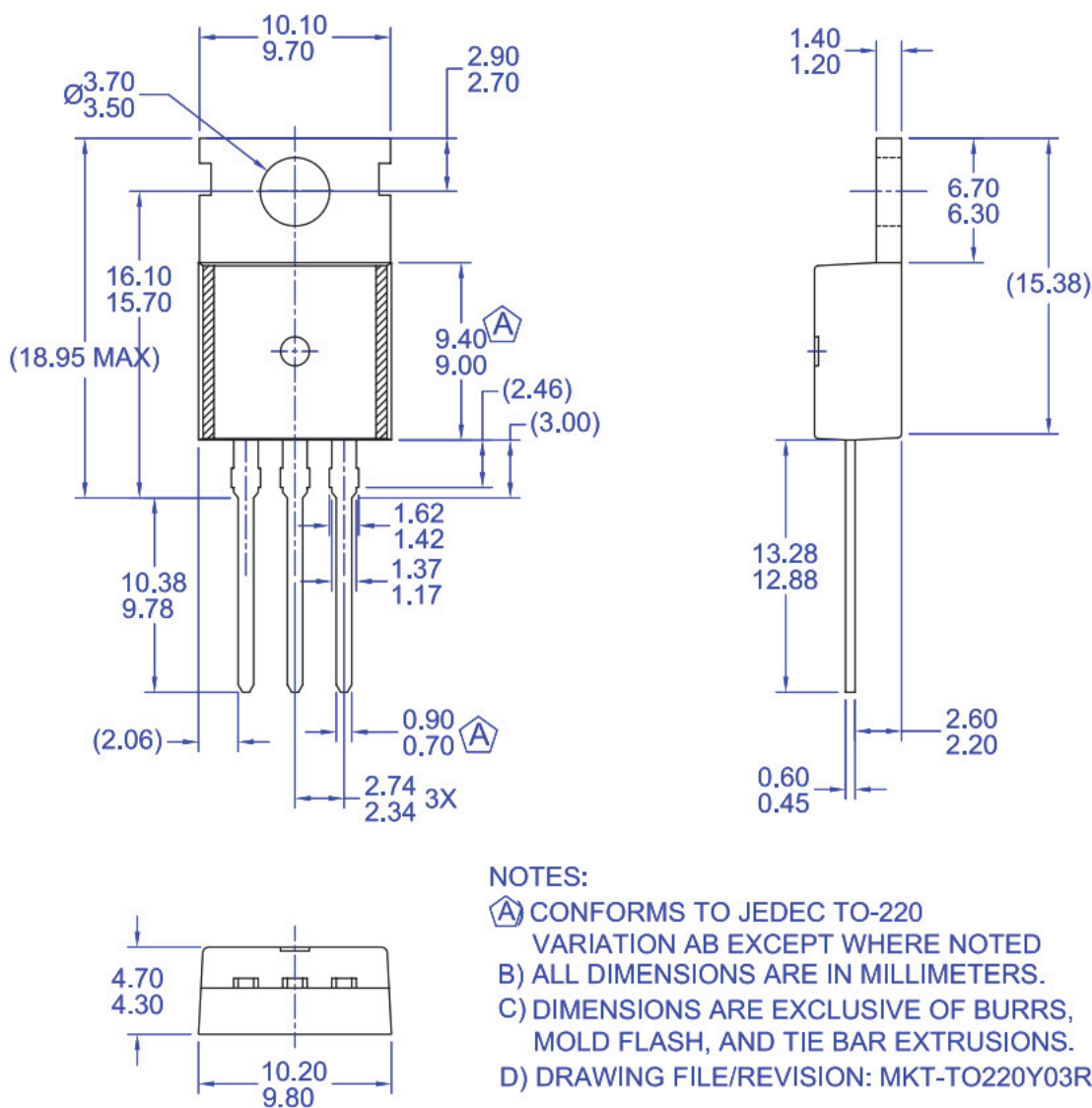


Figure 16. TO220, Molded, 3-Lead, Jedec Variation AB

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Mechanical Dimensions

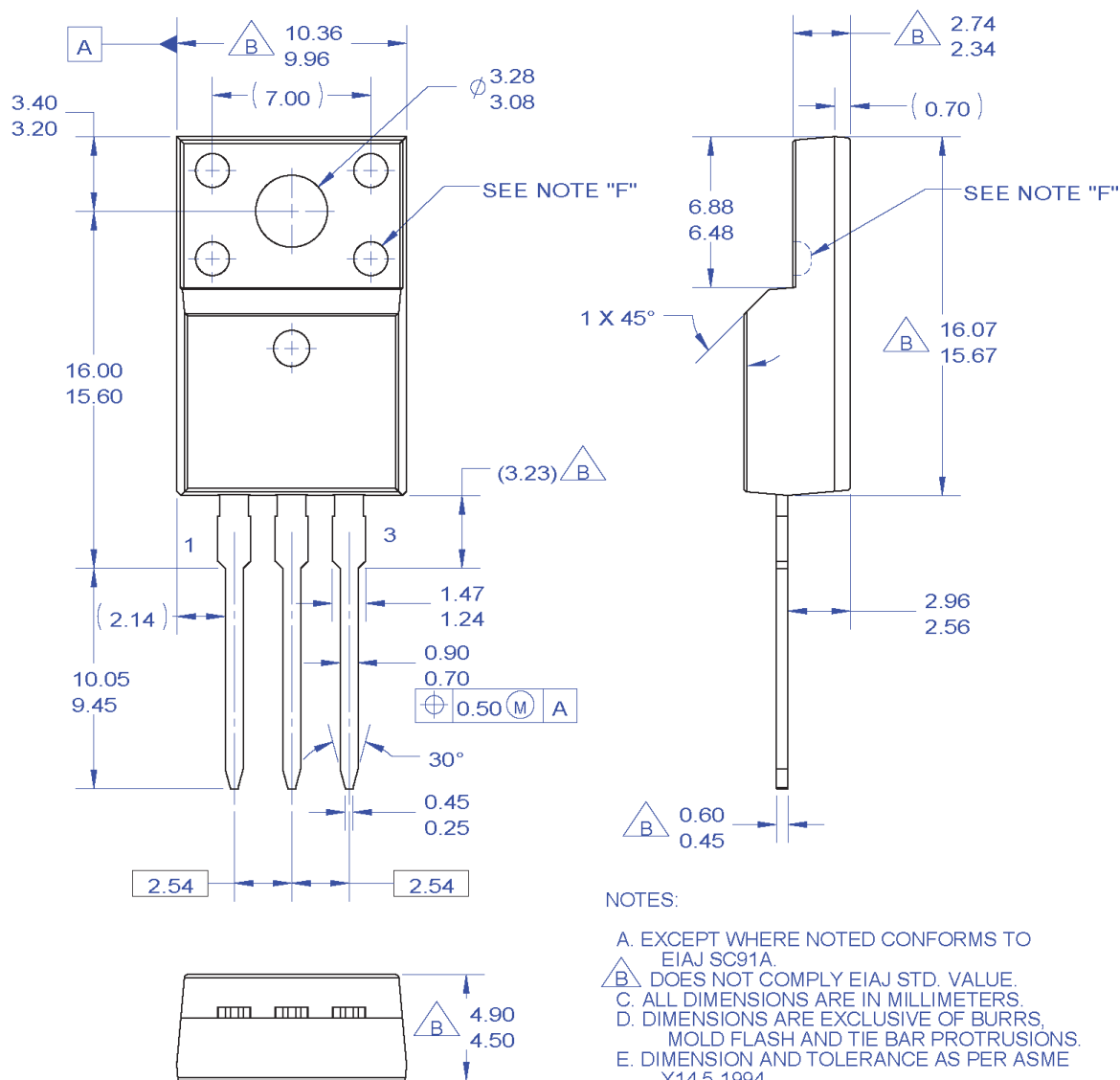


Figure 17. TO220, Molded, 3-Lead, Full Pack, EIAJ SC91, Straight Lead

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